



#16/ Amended  
Attorney  
8/20/01

Docket No. 740756-2064

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent application of: )  
Shunpei YAMAZAKI et al. )  
Serial No.: 09/437,135 ) Group Art Unit: 2813  
Filed: November 10, 1999 ) Examiner: E. Kielin  
For: SEMICONDUCTOR DEVICE AND ) Date: August 20, 2001  
METHOD FOR FORMING THE SAME)

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AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Responsive to the Office Action dated **March 20, 2001**, the period for response having been extended two (2) months to **August 20, 2001**, the following amendments and remarks are submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amended claims 1, 6, 11, 30, and 34 as follows. While claims 1, 6, 11, 30, and 34 are presented below in their amended form, the amendments to the above-noted claims are outlined in an Attachment to the Amendment using the conventional indication method of bracketing and underlining.

- sub 1
1. (Twice Amended) A method for manufacturing a semiconductor device comprising the steps of:
- forming a semiconductor film comprising amorphous silicon over a substrate;
  - crystallizing said semiconductor film by irradiating a laser light;
  - forming an insulating film on the crystallized semiconductor film by a vapor phase deposition; and
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